Monday, May 01, 2017

Hema Movva will receive the Best Paper Award at the 75th Device Research Conference (DRC), to be held June 25-28 at the University of Notre Dame. The DRC has brought together leading scientists, researchers, and students to share their latest discoveries in device science, technology and modeling for over seven decades. He is being recognized for his work "Room-Temperature Gate-Tunable Negative Differential resistance in MoS2/hBN/WSe2 Heterostructures," which was co-authored by S. Kang, A. Rai, K. Kim, B. Fallahazad, T. Taniguchi, K. Watanabe, E. Tutuc, and S.K. Banerjee. Movva previously received the Best Student Poster Award at the 2015 DRC for his poster titled "Top-gated WSe2 field-effect transistors with Pt contacts."

Movva is a graduate student at Texas ECE. He previously served as a research and development engineer at Solar Semiconductor (P) Ltd, as well as an engineering intern at Texas Instruments. He received his bachelor of Technology in Electrical Engineering from the Indian Institute of Technology, Bombay, in 2009.